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6. (Amended) A thin film transistor comprising:

a substrate;

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a gate including a double-layered structure having a first metal layer which is a bottom layer disposed on the substrate and a second metal layer disposed on the [substrate] first metal layer, the first metal layer including aluminum, the second metal layer being arranged on the first metal layer to prevent hillock at the sides of the aluminum first metal layer, the first metal layer being wider than the second metal layer by about 1 to 4 μm ;

a first insulating layer disposed on the substrate including the gate;

a semiconductor layer disposed on a portion of the first insulating layer at a location corresponding to the gate;

an ohmic contact layer disposed on two sides of the semiconductor layer;

a source electrode and a drain electrode disposed on the ohmic contact layer and extending onto the first insulating layer; and

a second insulating layer covering the semiconductor layer, the source and drain electrodes and the first insulating layer.

Please cancel claims 3, 7 and 9-26 without prejudice or disclaimer of the subject matter recited therein.